Low-Power, Low Noise and Distortion, Bipolar-Input AUDIO OPERATIONAL AMPLIFIERS

Check for Samples: OPA1662-Q1

FEATURES

- **Qualified for Automotive Applications**
- **AEC-Q100 Qualified With the Following Results**
  - **Device Temperature Grade 3: –40°C to 85°C Ambient Operating Temperature Range**
  - **Device HBM ESD Classification Level H2**
  - **Device CDM ESD Classification Level C3B**
- **Low Noise: 3.3 nV/√Hz at 1 kHz**
- **Low Distortion: 0.00006% at 1 kHz**
- **Low Quiescent Current: 1.5 mA per Channel**
- **Slew Rate: 17 V/µs**
- **Wide Gain Bandwidth: 22 MHz (G = +1)**
- **Unity Gain Stable**
- **Rail-to-Rail Output**
- **Wide Supply Range: ±1.5 V to ±18 V, or 3 V to 36 V**
- **Small Package Sizes: Dual: SO-8 and MSOP-8**

APPLICATIONS

- **Automotive**

DESCRIPTION

The OPA1662-Q1 (dual) bipolar-input operational amplifier achieves a low 3.3 nV/√Hz noise density with an ultralow distortion of 0.00006% at 1 kHz. The OPA1662-Q1 op amp offers rail-to-rail output swing to within 600 mV with 2-kΩ load, which increases headroom and maximizes dynamic range. This device also has a high output drive capability of ±30 mA.

The device operates over a very wide supply range of ±1.5 V to ±18 V, or 3 V to 36 V, on only 1.5 mA of supply current per channel. The OPA1662-Q1 op amp is unity-gain stable and provides excellent dynamic behavior over a wide range of load conditions.

The device also features completely independent circuitry for lowest crosstalk and freedom from interactions between channels, even when overdriven or overloaded.

The OPA1662-Q1 is specified from –40°C to 85°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

T_A	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	OPA1662AIDRQ1	O1662Q
–40°C to 85°C	OPA1662AIDGKRQ1	OUUI

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

Over operating free-air temperature range (unless otherwise noted).

		OPA1662-Q1	UNIT
Supply voltage, V_S = (V+) – (V–)		40	V
Input voltage		(V–) – 0.5 to (V+) + 0.5	V
Input current (all pins except power-supply pins)		±10	mA
Output short-circuit(2)		Continuous	
Operating temperature range		–40 to 125	°C
Storage temperature range		–65 to 150	°C
Junction temperature		200	°C
ESD ratings	Human body model (HBM) AEC-Q100 Classification Level H2	2	kV
	Charged device model (CDM) AEC-Q100 Classification Level C3B	750	V

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not supported.
(2) Short-circuit to V_S/2 (ground in symmetrical dual supply setups), one amplifier per package.

THERMAL INFORMATION

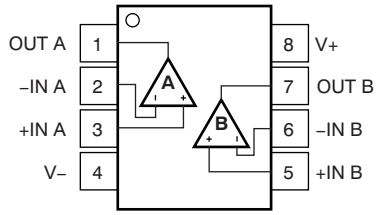
THERMAL METRIC(1)		OPA1662-Q1		UNIT
		D (SO)	DGK (MSOP)	
		8 PINS	8 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	156.3	225.4	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance	85.5	78.8	
θ_{JB}	Junction-to-board thermal resistance	64.9	110.5	
ψ_{JT}	Junction-to-top characterization parameter	33.8	14.6	
ψ_{JB}	Junction-to-board characterization parameter	64.3	108.5	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

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PIN CONFIGURATIONS

OPA1662-Q1: D AND DGK PACKAGES
SO-8 AND MSOP-8
(TOP VIEW)



ELECTRICAL CHARACTERISTICS: V_S = ±15 V

At T_A = 25°C and R_L = 2 kΩ, unless otherwise noted. V_{CM} = V_{OUT} = midsupply, unless otherwise noted.

PARAMETER		CONDITIONS		OPA1662-Q1 MIN	OPA1662-Q1 TYP	OPA1662-Q1 MAX	UNIT
AUDIO PERFORMANCE							
THD+N	Total harmonic distortion + noise	G = 1, f = 1 kHz, V_O = 3 V_{RMS}			0.00006		%
					–124		dB
IMD	Intermodulation distortion	G = 1, V_O = 3 V_{RMS}	SMPTE/DIN two-tone, 4:1 (60 Hz and 7 kHz)		0.00004		%
					–128		dB
			DIM 30 (3-kHz square wave and 15-kHz sine wave)		0.00004		%
					–128		dB
			CCIF twin-tone (19 kHz and 20 kHz)		0.00004		%
					–128		dB
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product	G = 1			22		MHz
SR	Slew rate	G = –1			17		V/µs
	Full power bandwidth(1)	V_O = 1 V_P			2.7		MHz
	Overload recovery time	G = –10			1		µs
	Channel separation (dual and quad)	f = 1 kHz			–120		dB
NOISE							
e_n	Input voltage noise	f = 20 Hz to 20 kHz			2.8		μV_{PP}
	Input voltage noise density	f = 1 kHz			3.3		$nV/\sqrt{Hz}$
		f = 100 Hz			5		$nV/\sqrt{Hz}$
I_n	Input current noise density	f = 1 kHz			1		$pA/\sqrt{Hz}$
		f = 100 Hz			2		$pA/\sqrt{Hz}$
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	V_S = ±1.5 V to ±18 V			±0.5	±1.5	mV
		V_S = ±1.5 V to ±18 V, T_A = –40°C to 85°(2)			2	8	µV/°C
PSRR	Power-supply rejection ratio	V_S = ±1.5 V to ±18 V			1	3	µV/V
INPUT BIAS CURRENT							
I_B	Input bias current	V_{CM} = 0 V			600	1200	nA
I_{OS}	Input offset current	V_{CM} = 0 V			±25	±100	nA
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode voltage range			(V–) + 0.5		(V+) – 1	V
CMRR	Common-mode rejection ratio			106	114		dB
INPUT IMPEDANCE							

(1) Full-power bandwidth = SR / (2π × V_P), where SR = slew rate.
(2) Specified by design and characterization.

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ELECTRICAL CHARACTERISTICS: V_S = ±15 V (continued)

At T_A = 25°C and R_L = 2 kΩ, unless otherwise noted. V_{CM} = V_{OUT} = midsupply, unless otherwise noted.

PARAMETER		CONDITIONS	OPA1662-Q1			UNIT
			MIN	TYP	MAX	
	Differential			170 || 2		kΩ || pF
	Common-mode			600 || 2.5		MΩ || pF
OPEN-LOOP GAIN						
A_{OL}	Open-loop voltage gain	(V–) + 0.6 V ≤ V_O ≤ (V+) – 0.6 V, R_L = 2 kΩ	106	114		dB
OUTPUT						
V_{OUT}	Output voltage	R_L = 2 kΩ	(V–) + 0.6		(V+) – 0.6	V
I_{OUT}	Output current		See Typical Characteristics			mA
Z_O	Open-loop output impedance		See Typical Characteristics			Ω
I_{SC}	Short-circuit current(3)			±50		mA
C_{LOAD}	Capacitive load drive			200		pF

(3) One channel at a time.

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ELECTRICAL CHARACTERISTICS: V_S = ±15 V (continued)

At T_A = 25°C and R_L = 2 kΩ, unless otherwise noted. V_{CM} = V_{OUT} = midsupply, unless otherwise noted.

PARAMETER		CONDITIONS	OPA1662-Q1 MIN	OPA1662-Q1 TYP	OPA1662-Q1 MAX	UNIT
POWER SUPPLY						
V_S	Specified voltage range		±1.5		±18	V
I_Q	Quiescent current (per channel)	I_{OUT} = 0 A		1.5	1.8	mA
		I_{OUT} = 0 A, T_A = –40°C to 85° (4)			2	mA
TEMPERATURE						
	Specified range		–40		85	°C

(4) Specified by design and characterization.

ELECTRICAL CHARACTERISTICS: V_S = 5 V

At T_A = 25°C and R_L = 2 kΩ, unless otherwise noted. V_{CM} = V_{OUT} = midsupply, unless otherwise noted.

PARAMETER		CONDITIONS		OPA1662-Q1 MIN	OPA1662-Q1 TYP	OPA1662-Q1 MAX	UNIT
AUDIO PERFORMANCE							
THD+N	Total harmonic distortion + noise	G = 1, f = 1 kHz, V_O = 3 V_{RMS}			0.0001		%
					–120		dB
IMD	Intermodulation distortion	G = 1, V_O = 3 V_{RMS}	SMPTE/DIN two-tone, 4:1 (60 Hz and 7 kHz)		0.00004		%
					–128		dB
			DIM 30 (3-kHz square wave and 15-kHz sine wave)		0.00004		%
					–128		dB
			CCIF twin-tone (19 kHz and 20 kHz)		0.00004		%
					–128		dB
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product	G = 1			20		MHz
SR	Slew rate	G = –1			13		V/µs
	Full power bandwidth (1)	V_O = 1 V_P			2		MHz
	Overload recovery time	G = –10			1		µs
	Channel separation (dual and quad)	f = 1 kHz			–120		dB
NOISE							
e_n	Input voltage noise	f = 20 Hz to 20 kHz			3.3		μV_{PP}
	Input voltage noise density	f = 1 kHz			3.3		$nV/\sqrt{Hz}$
		f = 100 Hz			5		$nV/\sqrt{Hz}$
I_n	Input current noise density	f = 1 kHz			1		$pA/\sqrt{Hz}$
		f = 100 Hz			2		$pA/\sqrt{Hz}$
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	V_S = ±1.5 V to ±18 V			±0.5	±1.5	mV
		V_S = ±1.5 V to ±18 V, T_A = –40°C to 85° (2)			2	8	µV/°C
PSRR	Power-supply rejection ratio	V_S = ±1.5 V to ±18 V			1	3	µV/V
INPUT BIAS CURRENT							
I_B	Input bias current	V_{CM} = 0 V			600	1200	nA
I_{OS}	Input offset current	V_{CM} = 0 V			±25	±100	nA
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode voltage range			(V–) + 0.5		(V+) – 1	V
CMRR	Common-mode rejection ratio			86	100		dB
INPUT IMPEDANCE							
	Differential				170 || 2		kΩ || pF
	Common-mode				600 || 2.5		MΩ || pF
OPEN-LOOP GAIN							

(1) Full-power bandwidth = SR / (2π × V_P), where SR = slew rate.
(2) Specified by design and characterization.

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ELECTRICAL CHARACTERISTICS: V_S = 5 V (continued)

At T_A = 25°C and R_L = 2 kΩ, unless otherwise noted. V_{CM} = V_{OUT} = midsupply, unless otherwise noted.

PARAMETER		CONDITIONS	OPA1662-Q1 MIN	OPA1662-Q1 TYP	OPA1662-Q1 MAX	UNIT
A_{OL}	Open-loop voltage gain	(V–) + 0.6 V ≤ V_O ≤ (V+) – 0.6 V, R_L = 2 kΩ	90	100		dB
OUTPUT						
V_{OUT}	Output voltage	R_L = 2 kΩ	(V–) + 0.6		(V+) – 0.6	V
I_{OUT}	Output current		See Typical Characteristics			mA
Z_O	Open-loop output impedance		See Typical Characteristics			Ω
I_{SC}	Short-circuit current(3)			±40		mA
C_{LOAD}	Capacitive load drive			200		pF
POWER SUPPLY						
V_S	Specified voltage range		±1.5		±18	V
I_Q	Quiescent current (per channel)	I_{OUT} = 0 A		1.4	1.7	mA
		I_{OUT} = 0 A, T_A = –40°C to 85°(2)			2	mA
TEMPERATURE						
	Specified range		–40		85	°C

(3) One channel at a time.

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TYPICAL CHARACTERISTICS

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

INPUT VOLTAGE NOISE DENSITY AND INPUT CURRENT NOISE DENSITY vs FREQUENCY

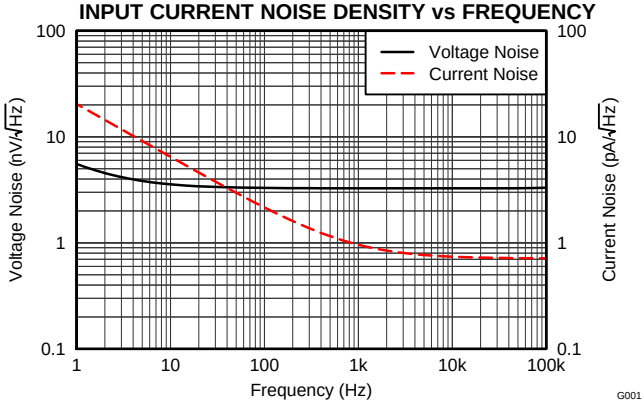


Figure 1.

0.1 Hz TO 10 Hz NOISE

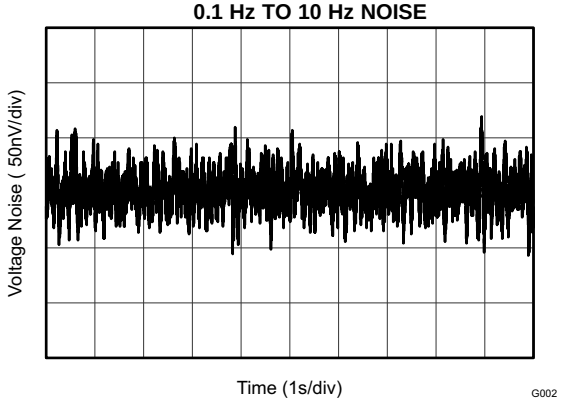


Figure 2.

VOLTAGE NOISE vs SOURCE RESISTANCE

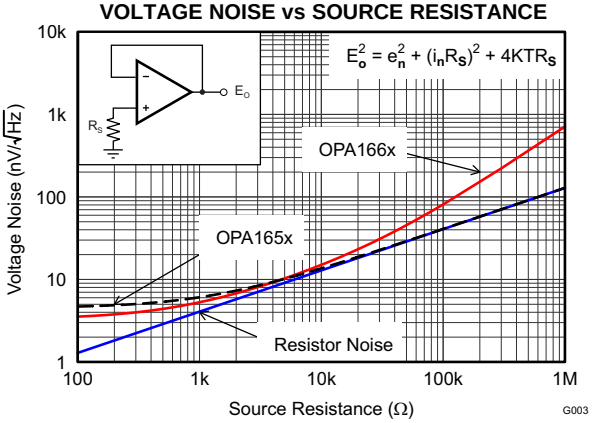


Figure 3.

MAXIMUM OUTPUT VOLTAGE vs FREQUENCY

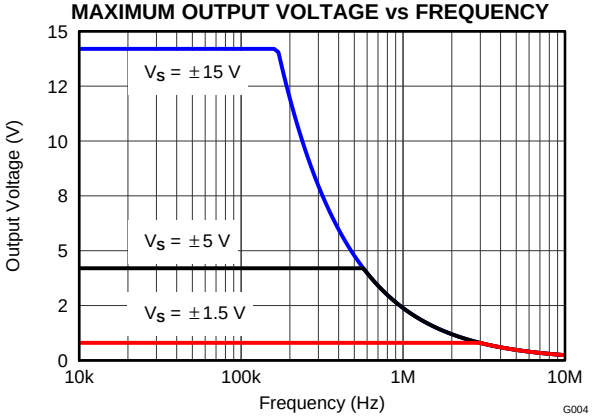


Figure 4.

GAIN AND PHASE vs FREQUENCY

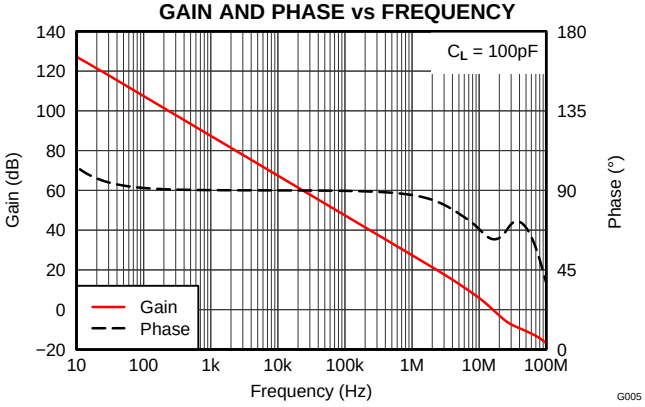


Figure 5.

CLOSED-LOOP GAIN vs FREQUENCY

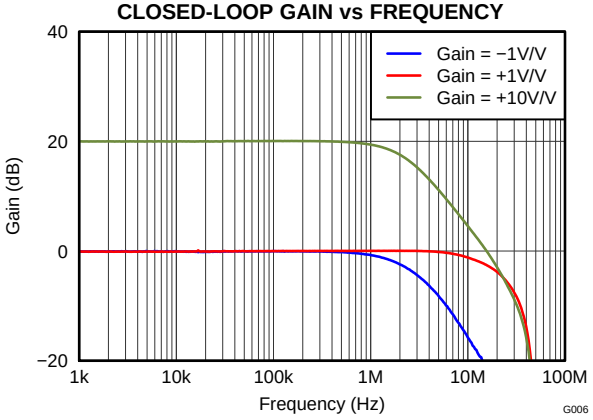


Figure 6.

TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

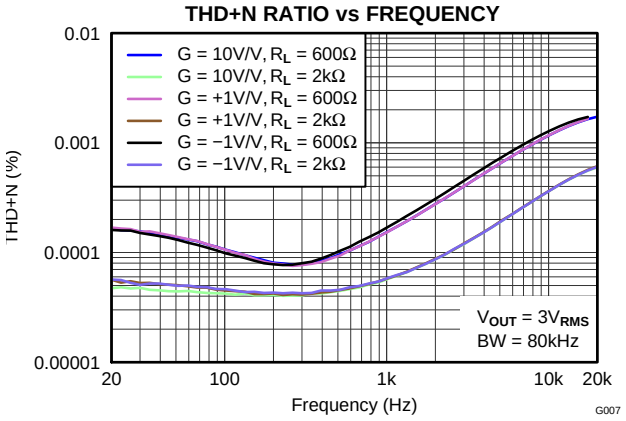


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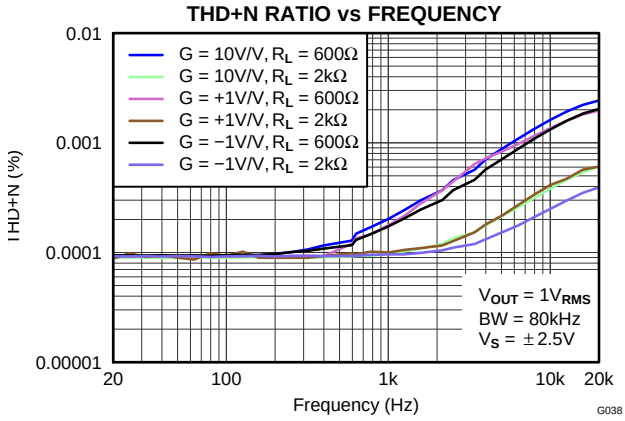


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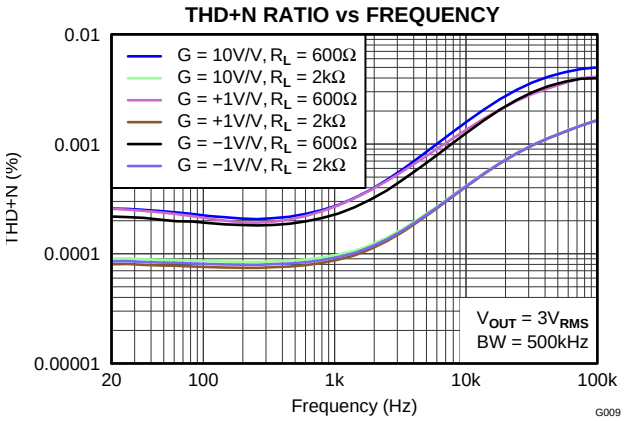


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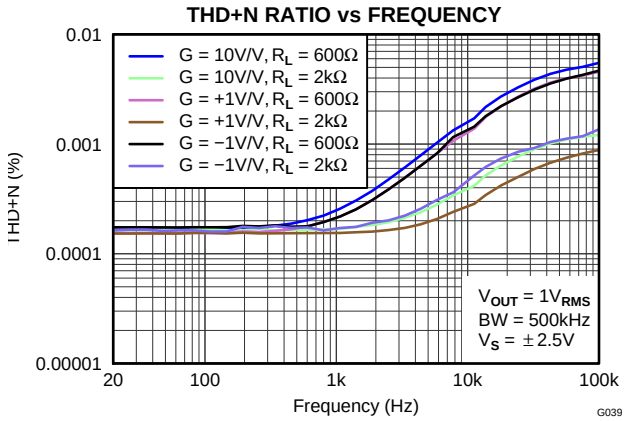


Figure 10.

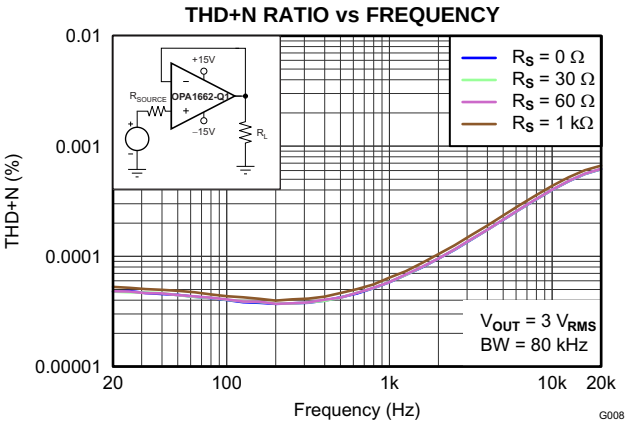


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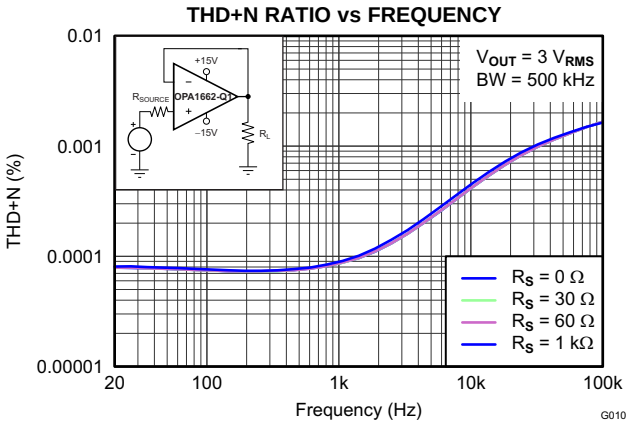


Figure 12.

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TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

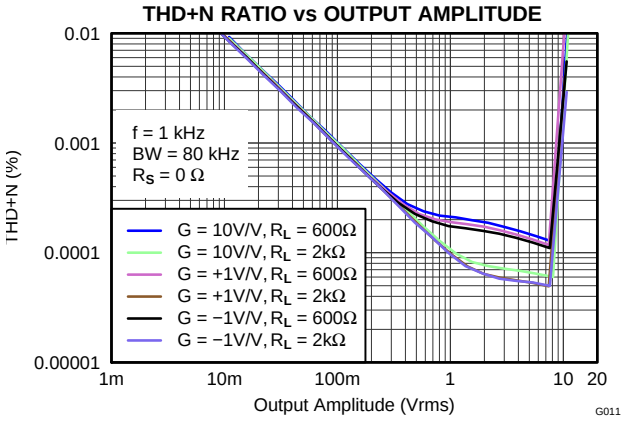


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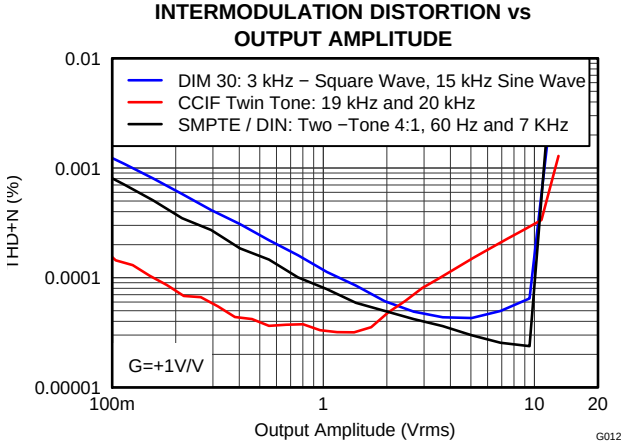


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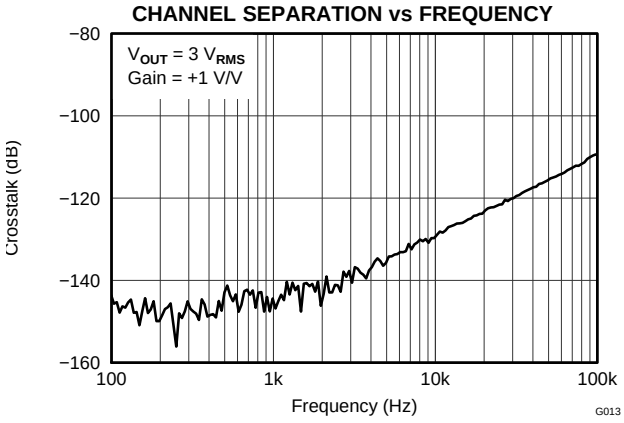


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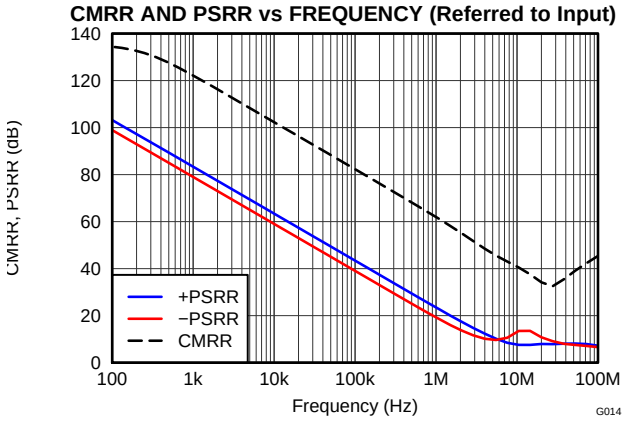


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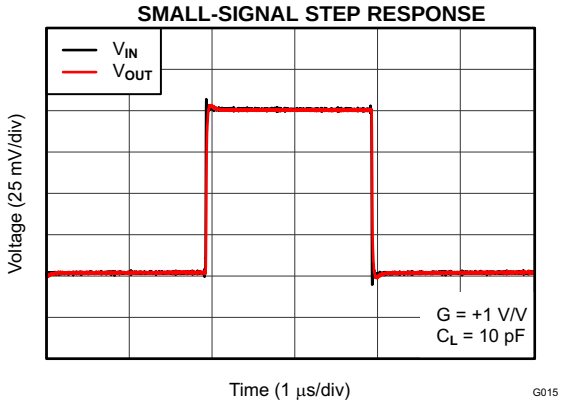


Figure 17.

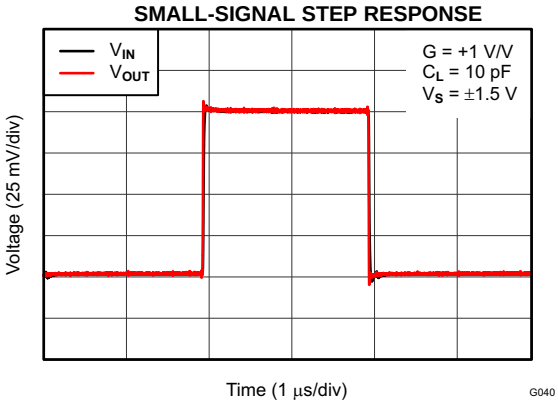


Figure 18.

TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

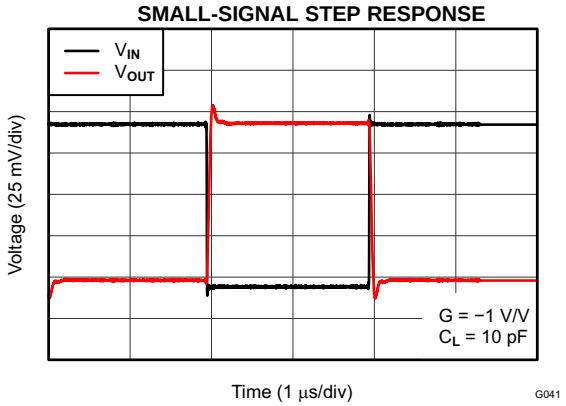


Figure 19.

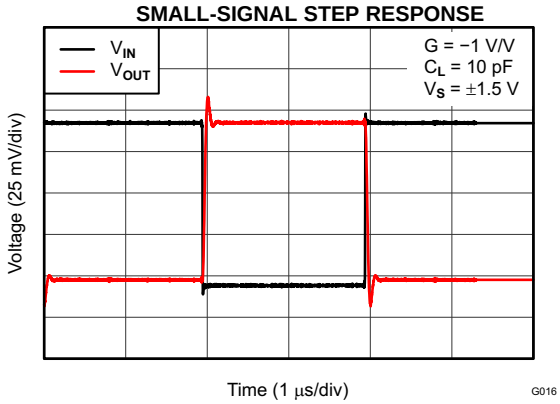


Figure 20.

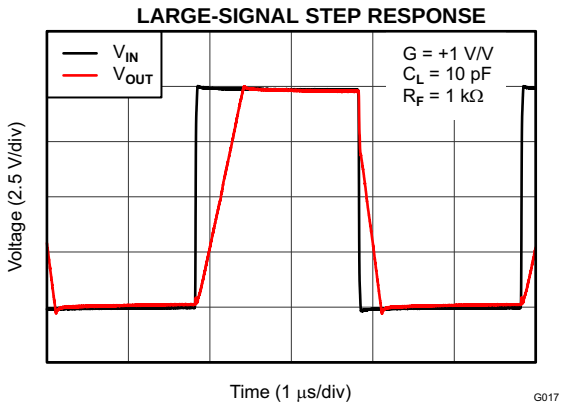


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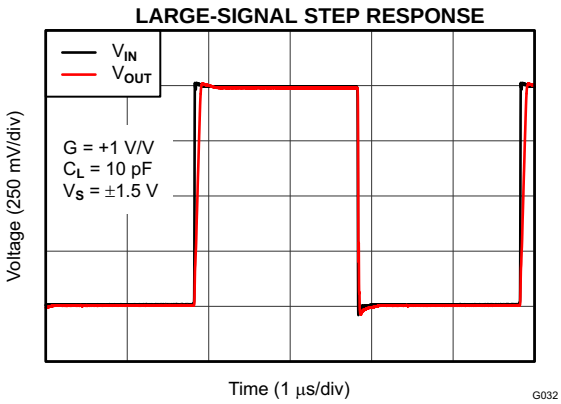


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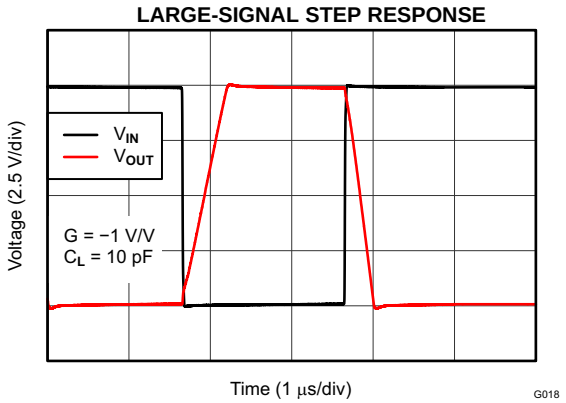


Figure 23.

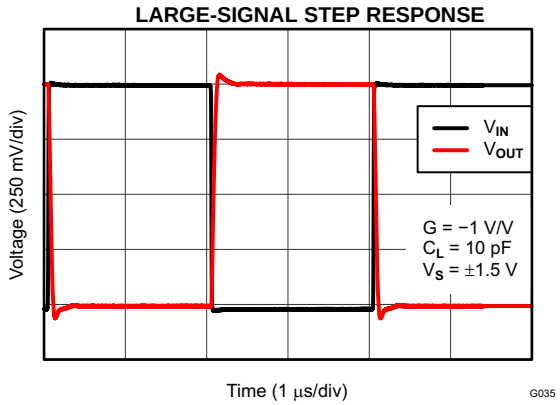


Figure 24.

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TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

SMALL-SIGNAL OVERSHOOT vs CAPACITIVE LOAD

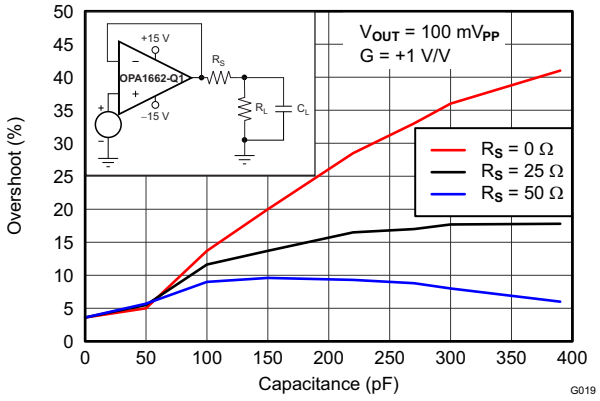


Figure 25.

SMALL-SIGNAL OVERSHOOT vs CAPACITIVE LOAD

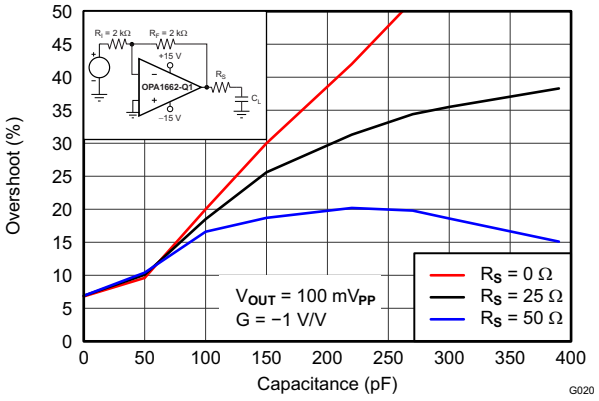


Figure 26.

SMALL-SIGNAL OVERSHOOT vs CAPACITIVE LOAD

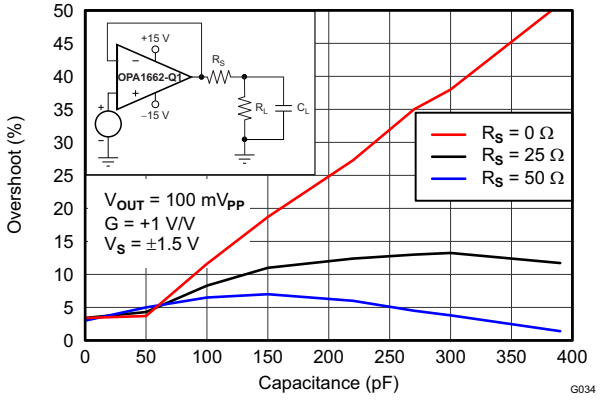


Figure 27.

SMALL-SIGNAL OVERSHOOT vs CAPACITIVE LOAD

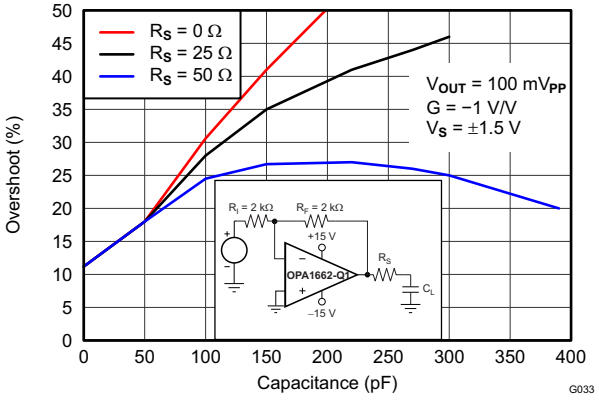


Figure 28.

SMALL-SIGNAL OVERSHOOT vs FEEDBACK CAPACITOR

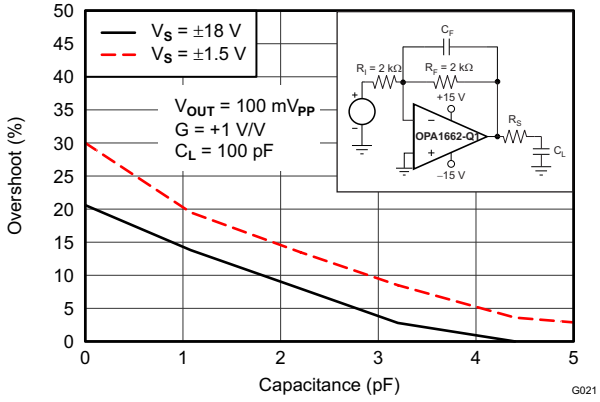


Figure 29.

PERCENT OVERSHOOT vs CAPACITIVE LOAD

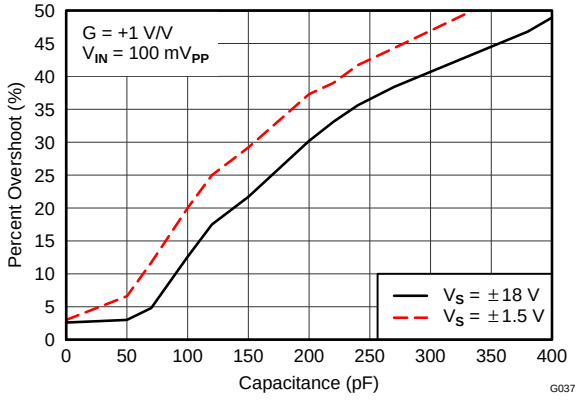


Figure 30.

TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

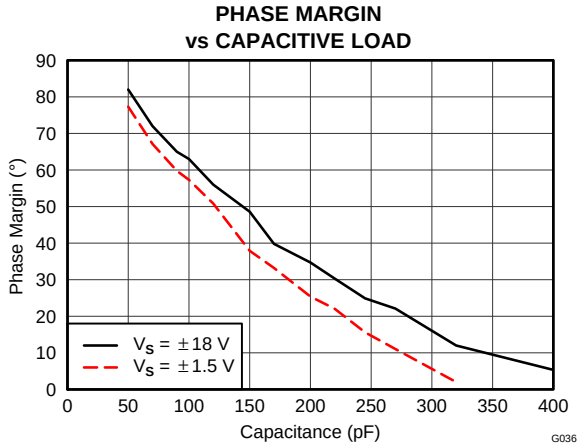


Figure 31.

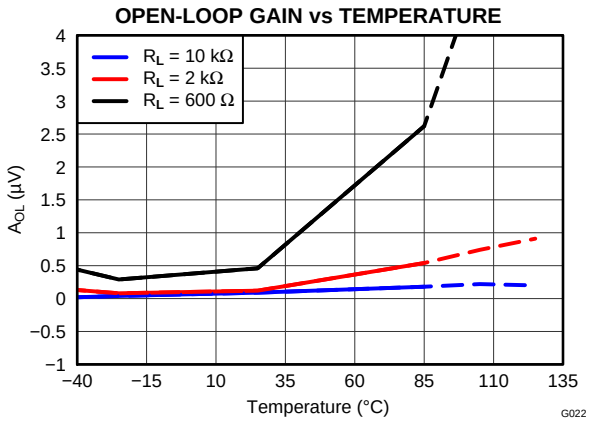


Figure 32.

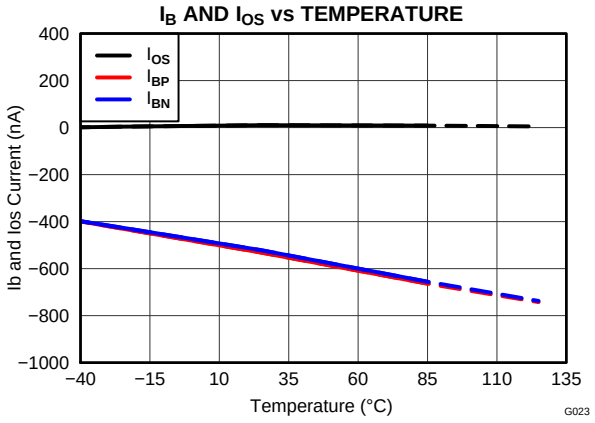


Figure 33.

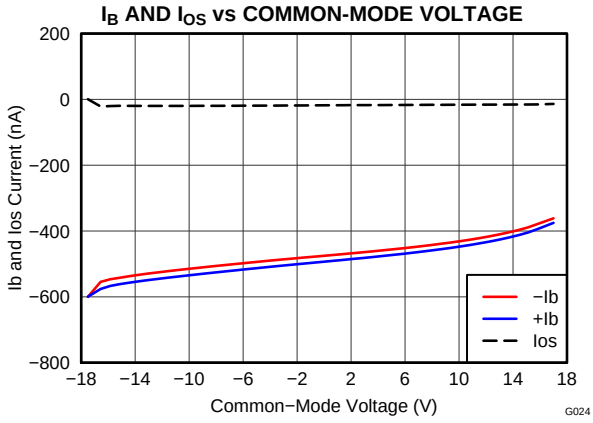


Figure 34.

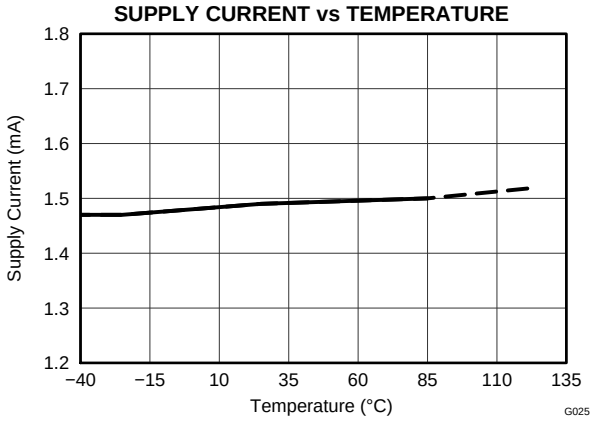


Figure 35.

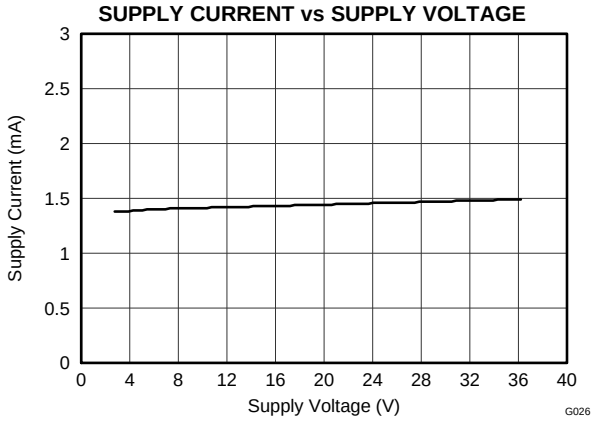


Figure 36.

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TYPICAL CHARACTERISTICS (continued)

At T_A = 25°C, V_S = ±15 V, and R_L = 2 kΩ, unless otherwise noted.

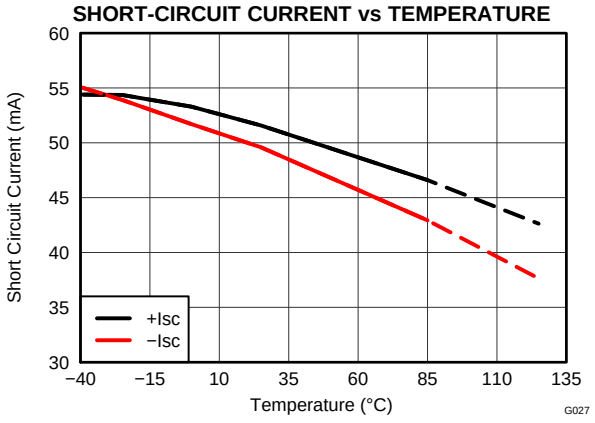


Figure 37.

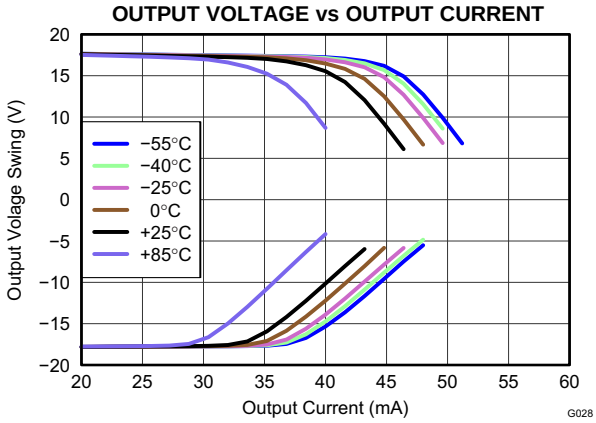


Figure 38.

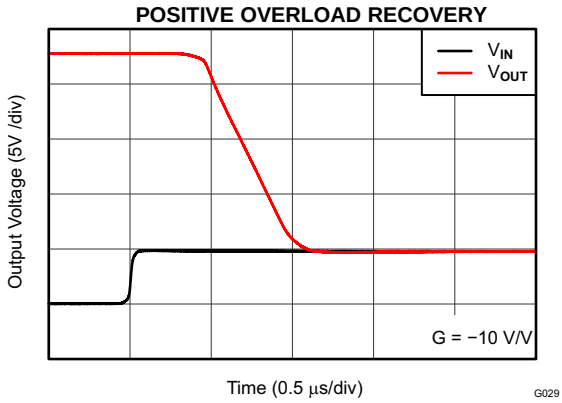


Figure 39.

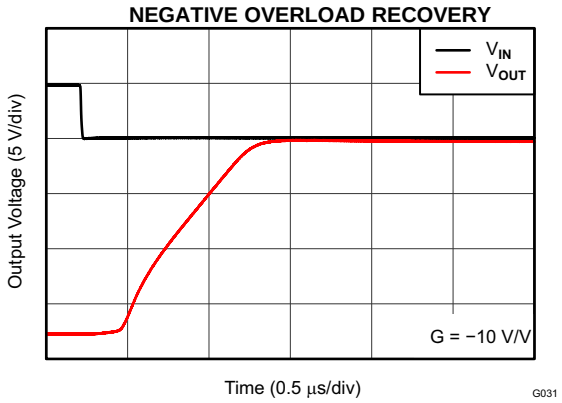


Figure 40.

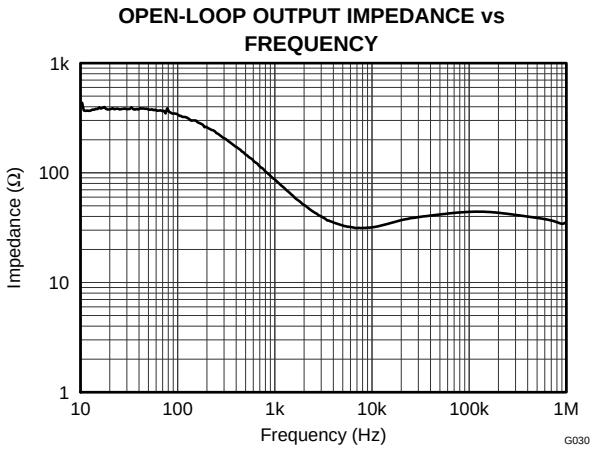


Figure 41.

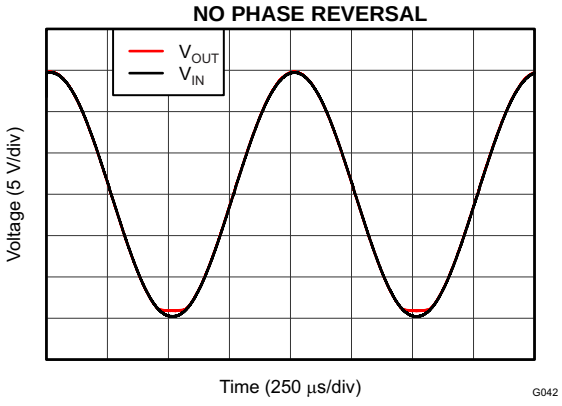


Figure 42.

APPLICATION INFORMATION

The OPA1662-Q1 is a unity-gain stable, precision dual and quad op amp with very low noise. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases, 0.1-µF capacitors are adequate. Figure 43 shows a simplified schematic of the OPA1662-Q1 (one channel shown).

OPERATING VOLTAGE

The OPA1662-Q1 op amp operates from ±1.5 V to ±18 V supplies while maintaining excellent performance. The OPA1662-Q1 can operate with as little as 3 V between the supplies and with up to 36 V between the supplies. However, some applications do not require equal positive and negative output voltage swing. With the OPA1662-Q1 device, power-supply voltages do not need to be equal. For example, the positive supply could be set to 25 V with the negative supply at –5 V.

In all cases, the common-mode voltage must be maintained within the specified range. In addition, key parameters are assured over the specified temperature range of T_A = –40°C to 85°C. Parameters that vary significantly with operating voltage or temperature are shown in the Typical Characteristics.

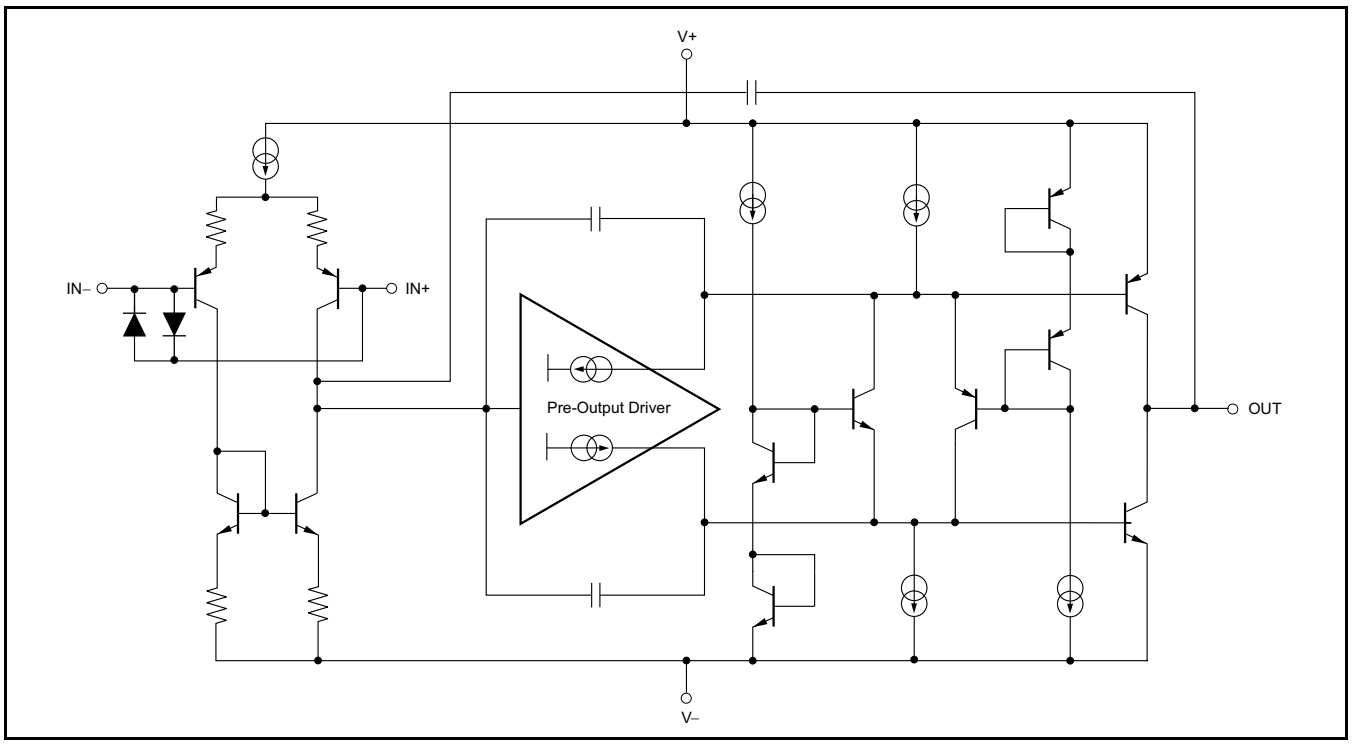


Figure 43. OPA1662-Q1 Simplified Schematic

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INPUT PROTECTION

The input terminals of the OPA1662-Q1 are protected from excessive differential voltage with back-to-back diodes, as Figure 44 illustrates. In most circuit applications, the input protection circuitry has no consequence. However, in low-gain or G = 1 circuits, fast ramping input signals can forward bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward bias condition, the input signal current must be limited to 10 mA or less. If the input signal current is not inherently limited, an input series resistor (R_I) and/or a feedback resistor (R_F) can be used to limit the signal input current. This resistor degrades the low-noise performance of the OPA1662-Q1 and is examined in the following *Noise Performance* section. Figure 44 shows an example configuration when both current-limiting input and feedback resistors are used.

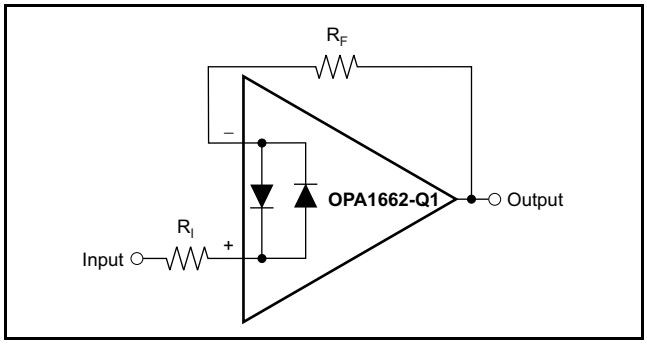


Figure 44. Pulsed Operation

NOISE PERFORMANCE

Figure 45 shows the total circuit noise for varying source impedances with the op amp in a unity-gain configuration (no feedback resistor network, and therefore no additional noise contributions).

The OPA1662-Q1 (GBW = 22 MHz, G = 1) is shown with total circuit noise calculated. The op amp itself contributes both a voltage noise component and a current noise component. The voltage noise is commonly modeled as a time-varying component of the offset voltage. The current noise is modeled as the time-varying component of the input bias current and reacts with the source resistance to create a voltage component of noise. Therefore, the lowest noise op amp for a given application depends on the source impedance. For low source impedance, current noise is negligible, and voltage noise generally dominates. The low voltage noise of the OPA1662-Q1 op amp makes them a better choice for low source impedances of less than 1 kΩ.

The equation in Figure 45 shows the calculation of the total circuit noise, with these parameters:

- e_n = Voltage noise
- i_n = Current noise
- R_S = Source impedance
- k = Boltzmann's constant = 1.38 × 10^{-23} J/K
- T = Temperature in Kelvins (K)

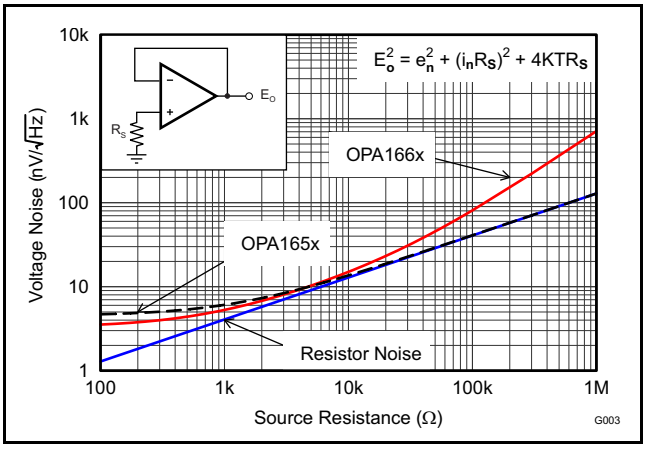


Figure 45. Noise Performance of the OPA1662-Q1 in Unity-Gain Buffer Configuration

BASIC NOISE CALCULATIONS

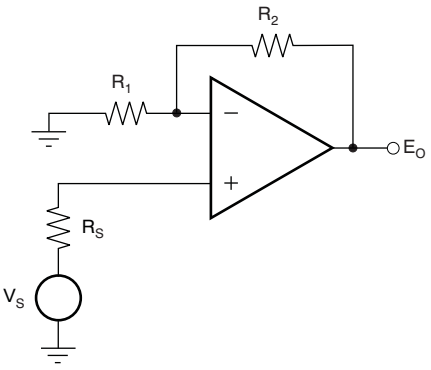
Design of low-noise op amp circuits requires careful consideration of a variety of possible noise contributors: noise from the signal source, noise generated in the op amp, and noise from the feedback network resistors. The total noise of the circuit is the root-sum-square combination of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. Figure 45 plots this equation. The source impedance is usually fixed; consequently, select the op amp and the feedback resistors to minimize the respective contributions to the total noise.

Figure 46 illustrates both inverting and noninverting op amp circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise. The current noise of the op amp reacts with the feedback resistors to create additional noise components. The feedback resistor values can generally be chosen to make these noise sources negligible. The equations for total noise are shown for both configurations.

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A) Noise in Noninverting Gain Configuration



Noise at the output:

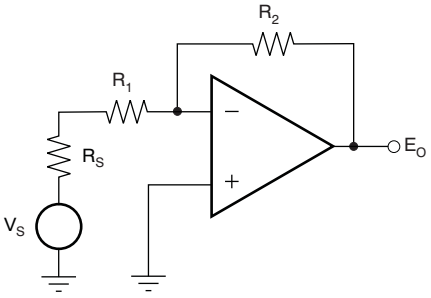
$$E_O^2 = \left(1 + \frac{R_2}{R_1}\right)^2 e_n^2 + \left(\frac{R_2}{R_1}\right)^2 e_1^2 + e_2^2 + \left(1 + \frac{R_2}{R_1}\right)^2 e_s^2$$

Where $e_S = \sqrt{4kTR_S}$ = thermal noise of R_S

$e_1 = \sqrt{4kTR_1}$ = thermal noise of R_1

$e_2 = \sqrt{4kTR_2}$ = thermal noise of R_2

B) Noise in Inverting Gain Configuration



Noise at the output:

$$E_O^2 = \left(1 + \frac{R_2}{R_1 + R_S}\right)^2 e_n^2 + \left(\frac{R_2}{R_1 + R_S}\right)^2 e_1^2 + e_2^2 + \left(\frac{R_2}{R_1 + R_S}\right)^2 e_s^2$$

Where $e_S = \sqrt{4kTR_S}$ = thermal noise of R_S

$e_1 = \sqrt{4kTR_1}$ = thermal noise of R_1

$e_2 = \sqrt{4kTR_2}$ = thermal noise of R_2

Note: For the OPA1662-Q1 op amp at 1 kHz, e_n = 3.3 nV/$\sqrt{\text{Hz}}$.

Figure 46. Noise Calculation in Gain Configurations

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TOTAL HARMONIC DISTORTION MEASUREMENTS

The OPA1662-Q1 op amp has excellent distortion characteristics. THD + noise is below 0.0006% (G = 1, V_O = 3 V_{RMS}, BW = 80 kHz) throughout the audio frequency range, 20 Hz to 20 kHz, with a 2-kΩ load (see Figure 7 for characteristic performance).

The distortion produced by the OPA1662-Q1 op amp is below the measurement limit of many commercially available distortion analyzers. However, a special test circuit (such as Figure 47 shows) can be used to extend the measurement capabilities.

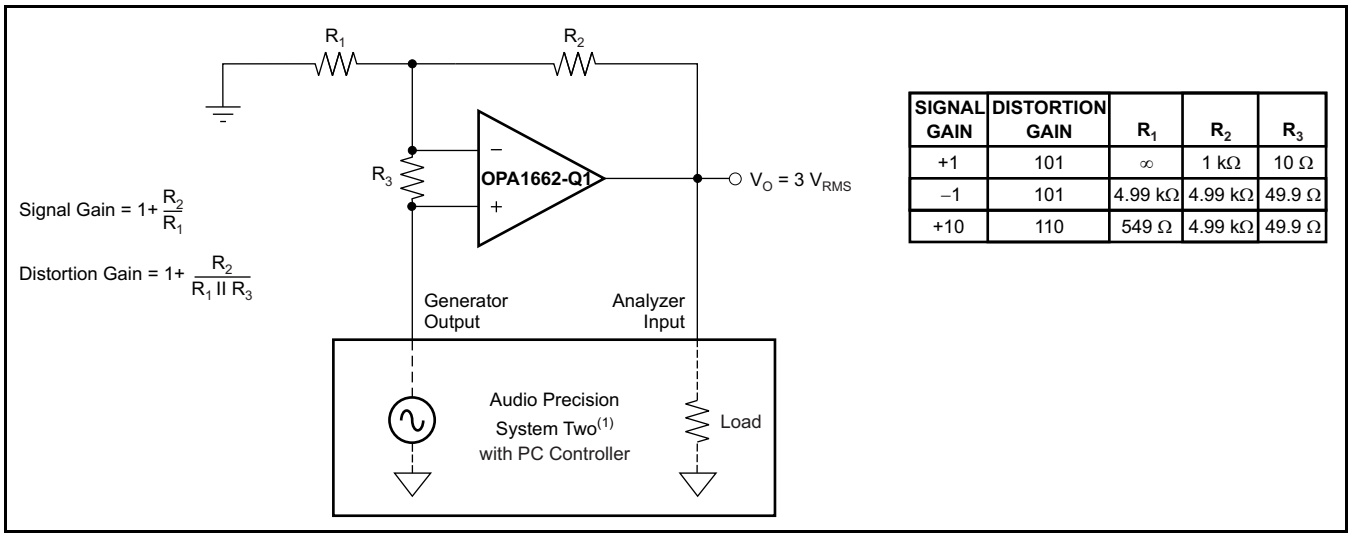
Op amp distortion can be considered an internal error source that can be referred to the input. Figure 47 shows a circuit that causes the op amp distortion to be gained up (refer to the table in Figure 47 for the distortion gain factor for various signal gains). The addition of R_3 to the otherwise standard noninverting amplifier configuration alters the feedback factor or noise gain of the circuit. The closed-loop gain is unchanged, but the feedback available for error correction is reduced by the distortion gain factor, thus extending the resolution by the same amount. Note that the input signal and load applied to the op amp are the same as with conventional feedback without R_3. The value of R_3 should be kept small to minimize its effect on the distortion measurements.

The validity of this technique can be verified by duplicating measurements at high gain and/or high frequency where the distortion is within the measurement capability of the test equipment. Measurements for this data sheet were made with an Audio Precision System Two distortion/noise analyzer, which greatly simplifies such repetitive measurements. The measurement technique can, however, be performed with manual distortion measurement instruments.

CAPACITIVE LOADS

The dynamic characteristics of the OPA1662-Q1 have been optimized for commonly encountered gains, loads, and operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (R_S equal to 50 Ω, for example) in series with the output.

This small series resistor also prevents excess power dissipation if the output of the device becomes shorted. Figure 25 illustrates a graph of *Small-Signal Overshoot vs Capacitive Load* for several values of R_S. Also, refer to Applications Bulletin AB-028 (literature number SBOA015, available for download from the TI web site) for details of analysis techniques and application circuits.



SIGNAL GAIN	DISTORTION GAIN	R_1	R_2	R_3
+1	101	∞	1 kΩ	10 Ω
–1	101	4.99 kΩ	4.99 kΩ	49.9 Ω
+10	110	549 Ω	4.99 kΩ	49.9 Ω

(1) For measurement bandwidth, see Figure 7 through Figure 12.

Figure 47. Distortion Test Circuit

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POWER DISSIPATION

The OPA1662-Q1 op amp is capable of driving 2-kΩ loads with a power-supply voltage up to ±18 V and full operating temperature range. Internal power dissipation increases when operating at high supply voltages. Copper leadframe construction used in the OPA1662-Q1 op amp improves heat dissipation compared to conventional materials. Circuit board layout can also help minimize junction temperature rise. Wide copper traces help dissipate the heat by acting as an additional heat sink. Temperature rise can be further minimized by soldering the devices to the circuit board rather than using a socket.

ELECTRICAL OVERSTRESS

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

It is helpful to have a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event. Figure 48 illustrates the ESD circuits contained in the OPA1662-Q1 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as it discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent it from being damaged. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more of the amplifier device pins, current flows through one or more of the steering diodes. Depending on the path that the current takes, the absorption device may activate. The absorption device internal to the OPA1662-Q1 triggers when a fast ESD voltage pulse is impressed across the supply pins. Once triggered, it quickly activates, clamping the ESD pulse to a safe voltage level.

When the operational amplifier connects into a circuit such as that illustrated in Figure 48, the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. Should this condition occur, there is a risk that some of the internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through steering diode paths and rarely involves the absorption device.

Figure 48 depicts a specific example where the input voltage, V_{IN}, exceeds the positive supply voltage ($+V_S$) by 500 mV or more. Much of what happens in the circuit depends on the supply characteristics. If $+V_S$ can sink the current, one of the upper input steering diodes conducts and directs current to $+V_S$. Excessively high current levels can flow with increasingly higher V_{IN}. As a result, the datasheet specifications recommend that applications limit the input current to 10 mA.

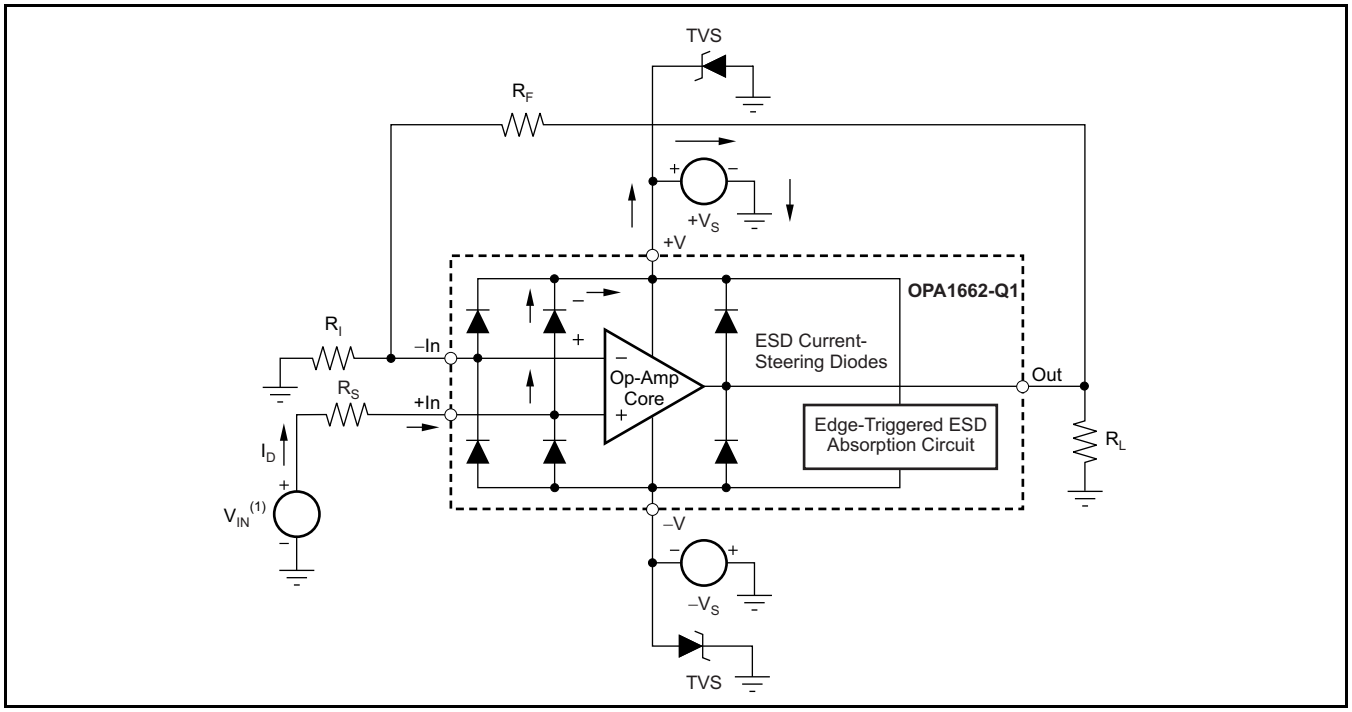
If the supply is not capable of sinking the current, V_{IN} may begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings. In extreme but rare cases, the absorption device triggers on while $+V_S$ and $–V_S$ are applied. If this event happens, a direct current path is established between the $+V_S$ and $–V_S$ supplies. The power dissipation of the absorption device is quickly exceeded, and the extreme internal heating destroys the operational amplifier.

Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies $+V_S$ and/or $–V_S$ are at 0 V. Again, it depends on the supply characteristic while at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the operational amplifier supply current may be supplied by the input source via the current steering diodes. This state is not a normal bias condition; the amplifier most likely will not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.

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If there is an uncertainty about the ability of the supply to absorb this current, external zener diodes may be added to the supply pins as shown in Figure 48.

The zener voltage must be selected such that the diode does not turn on during normal operation. However, its zener voltage should be low enough so that the zener diode conducts if the supply pin begins to rise above the safe operating supply voltage level.



(1) $V_{IN} = +V_S + 500mV$.

Figure 48. Equivalent Internal ESD Circuitry and Its Relation to a Typical Circuit Application (Single Channel Shown)

APPLICATION CIRCUIT

An additional application idea is shown in Figure 49.

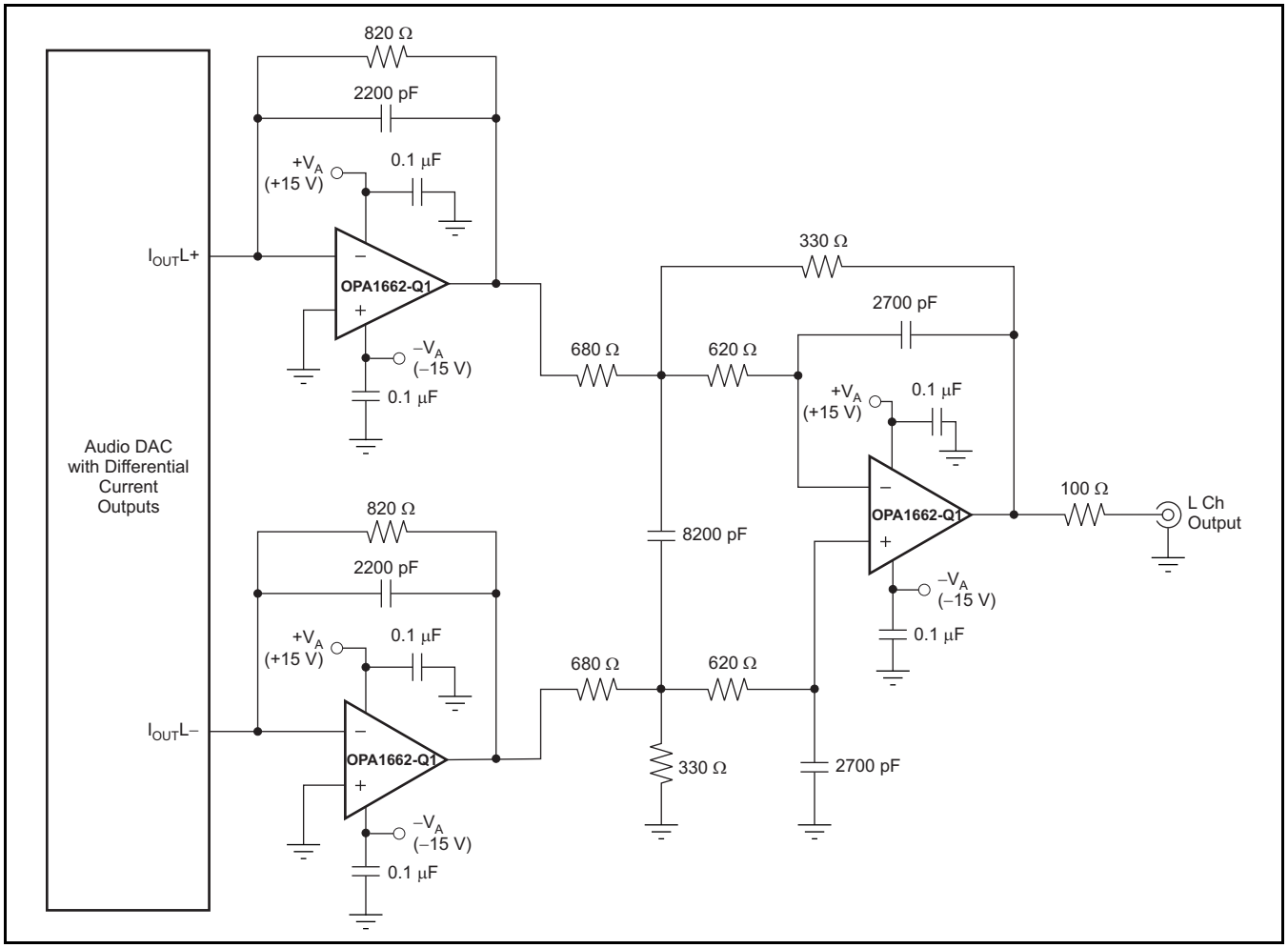


Figure 49. Audio DAC I/V Converter and Output Filter

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REVISION HISTORY

Changes from Revision A (September, 2012) to Revision B **Page**

- Changed Grade 1 to Grade 3 in Features 1
- Changed top-side marking for OPA1662AIDRQ1 from preview to O1662Q 2

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
OPA1662AIDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	OUUI	Samples
OPA1662AIDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	O1662Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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OTHER QUALIFIED VERSIONS OF OPA1662-Q1 :

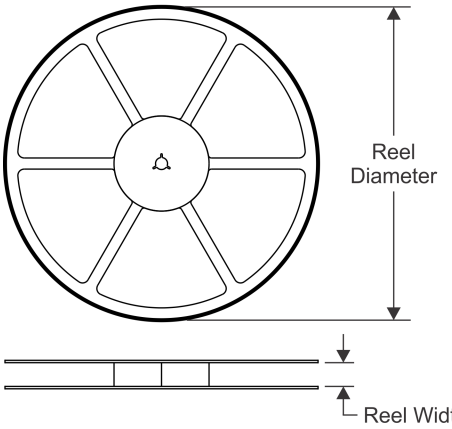
- Catalog: OPA1662

NOTE: Qualified Version Definitions:

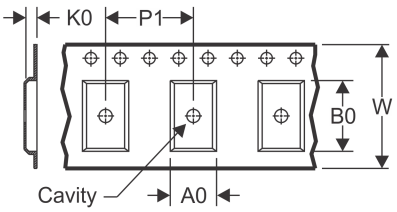
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

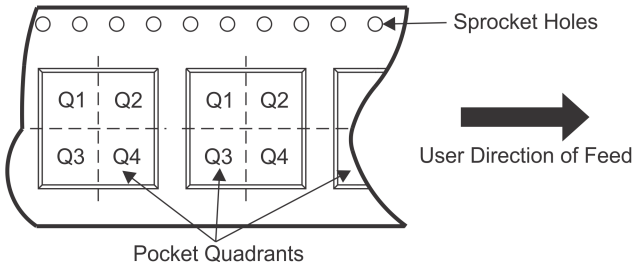


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

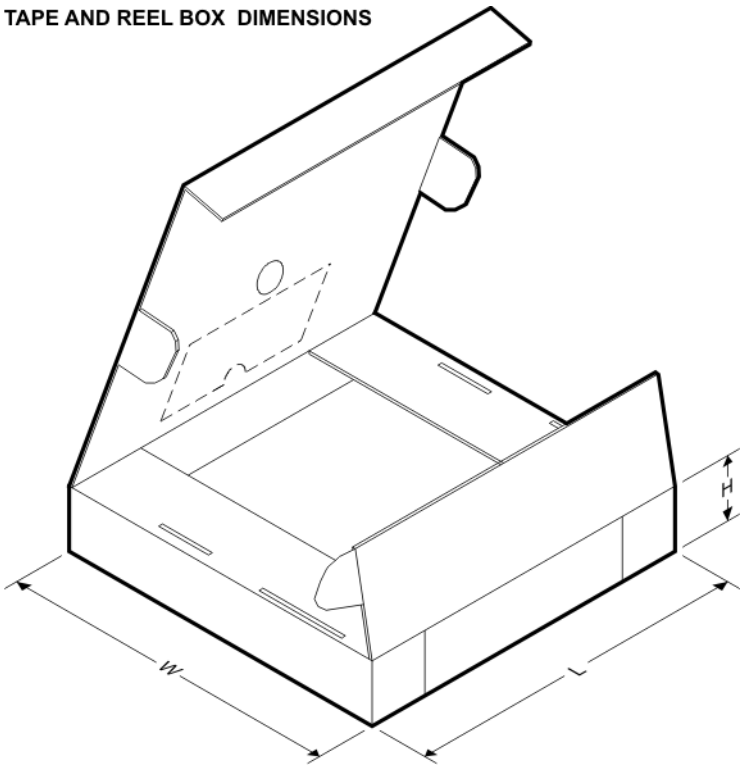
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA1662AIDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA1662AIDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

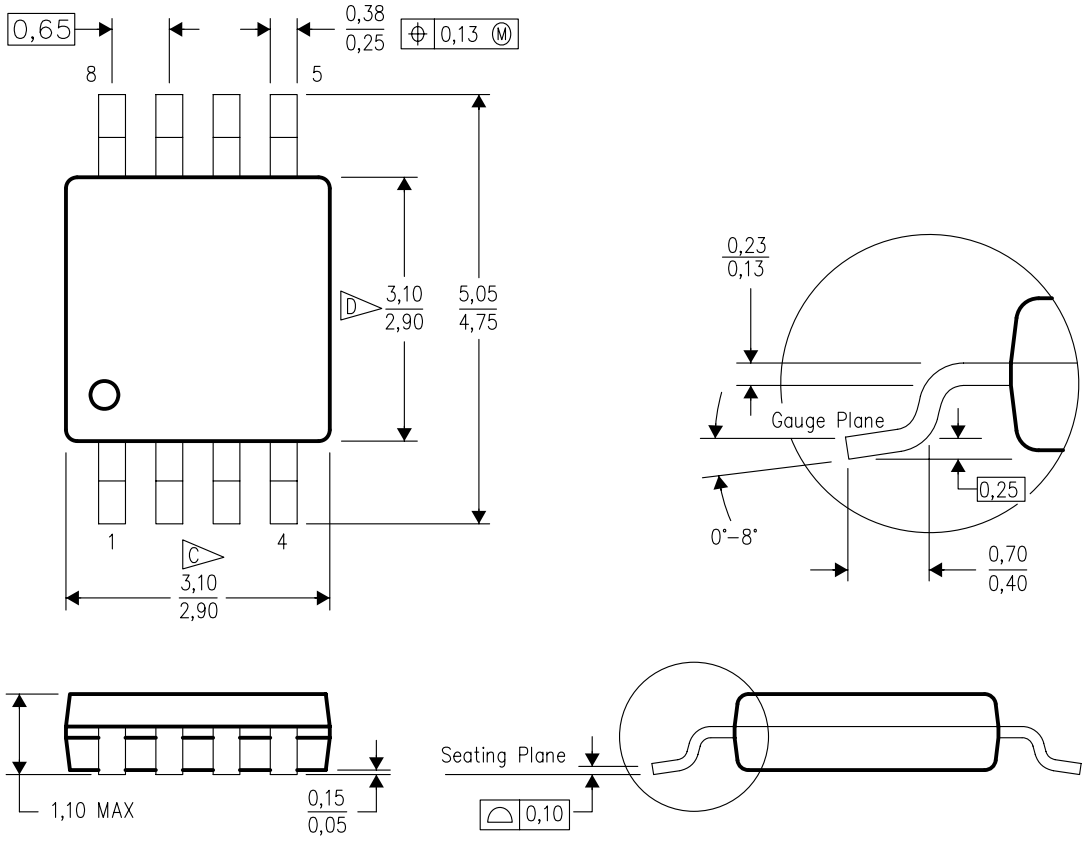
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA1662AIDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA1662AIDRQ1	SOIC	D	8	2500	367.0	367.0	35.0

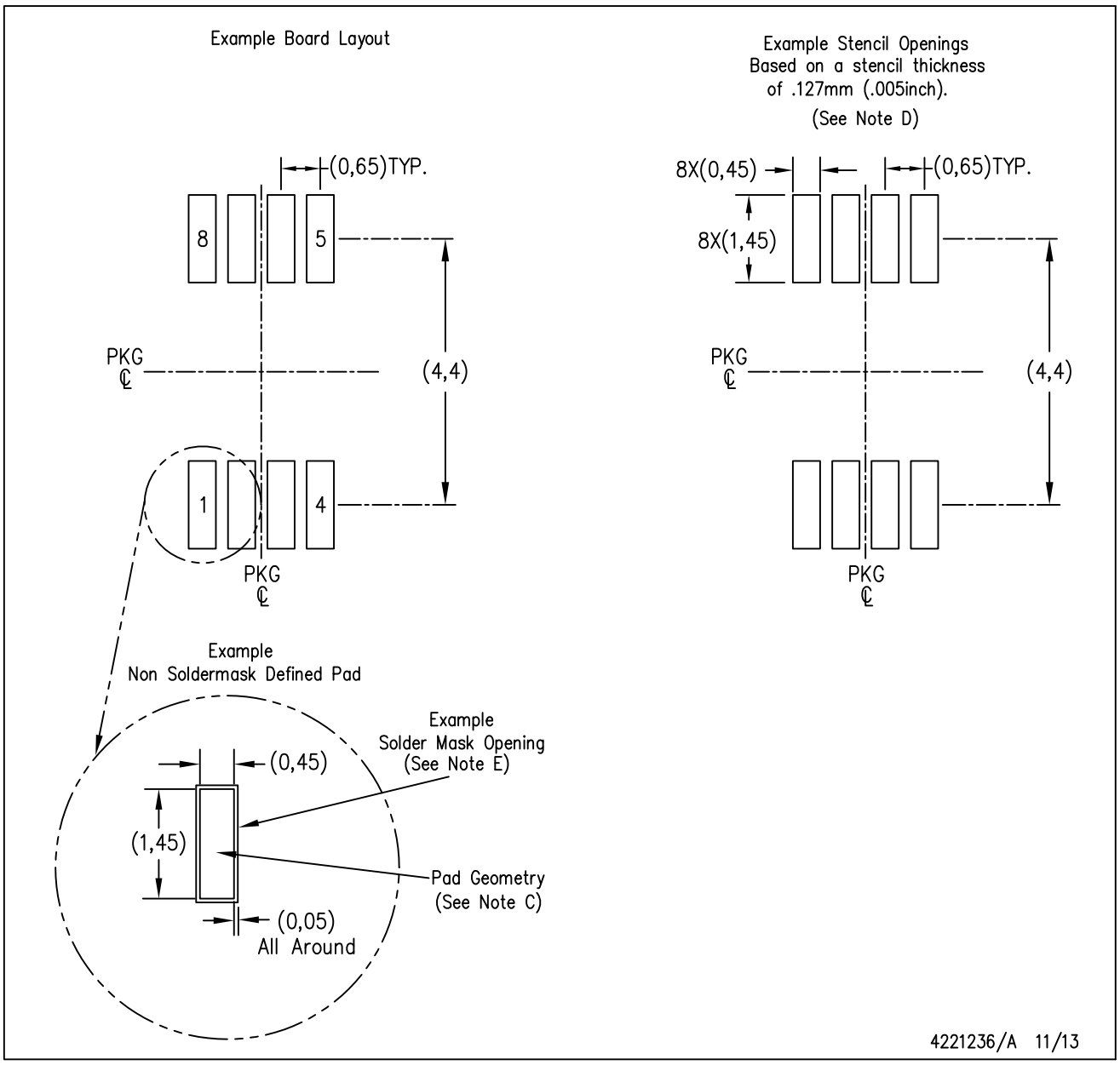
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



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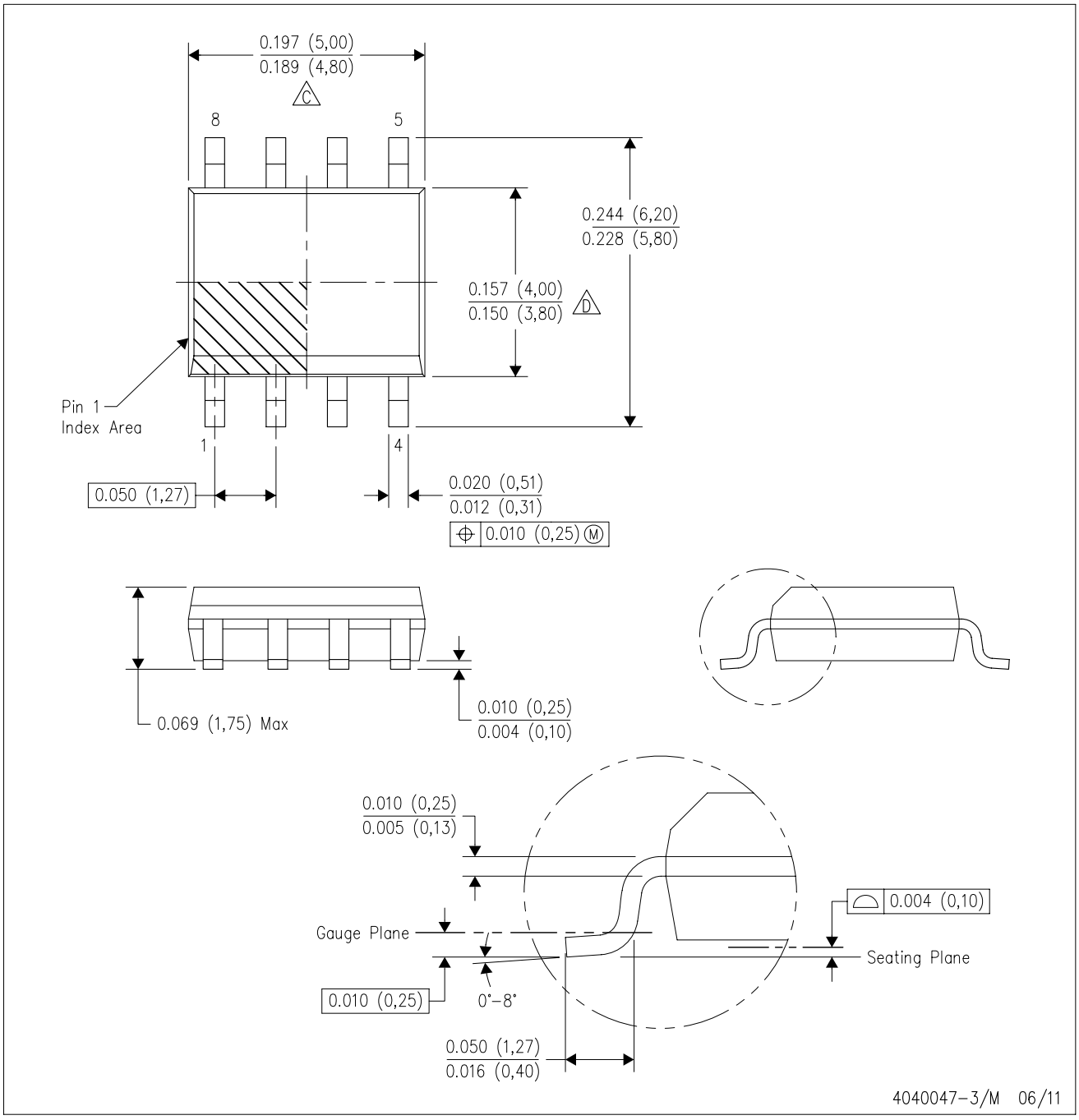
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



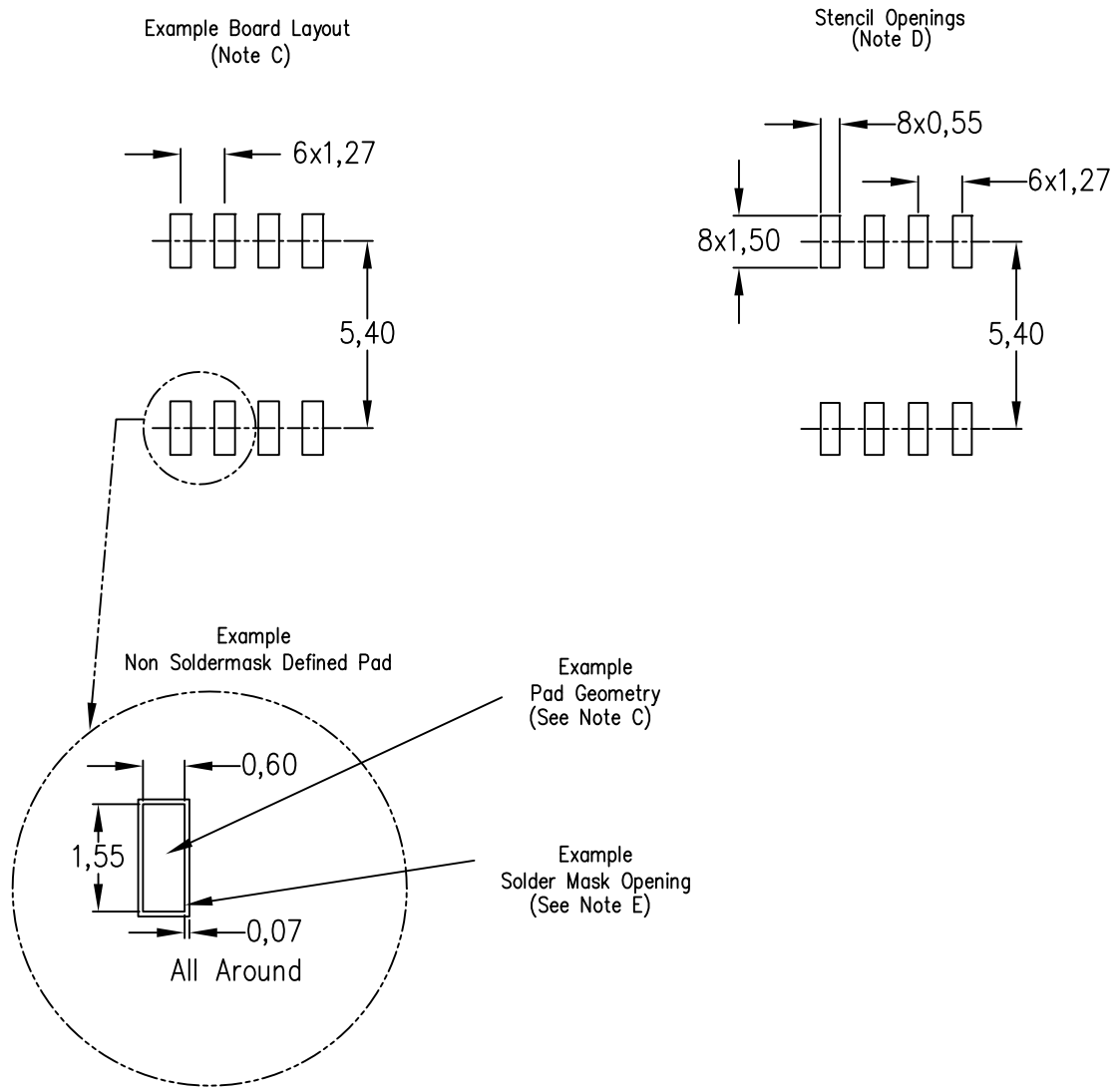
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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